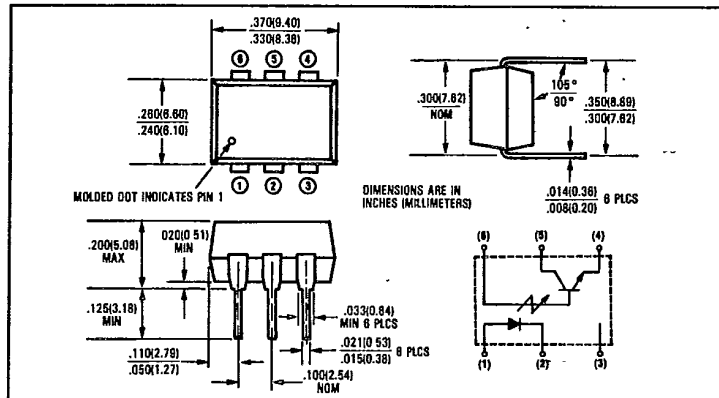
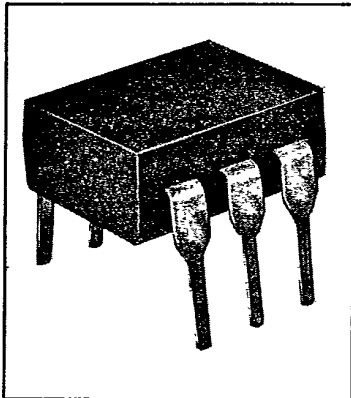


T-41-83

Optically Coupled Isolators

Types OPI2152, OPI2252



Features

- 1500 or 2500 volt isolation
- High current transfer ratio
- Low cost 6 pin dual-in-line package
- UL recognized File No. E58730

Description

The OPI2152 and OPI2252 each consist of a gallium arsenide infrared light emitting diode coupled to an NPN silicon phototransistor mounted in a six pin dual-in-line package. The OPI2152 and OPI2252 are identical except for input-to-output isolation voltage.

Absolute Maximum Ratings (TA = 25°C unless otherwise noted)

Input-to-Output Isolation Voltage OPI2152	± 1500 VDC ⁽¹⁾
OPI2252	± 2500 VDC ⁽¹⁾
Storage Temperature Range	-55°C to +150°C
Operating Temperature Range	-55°C to +100°C
Lead Soldering Temperature (1/16 inch (1.6 mm) from case for 5 sec. with soldering iron) ⁽²⁾	260°C

Input Diode

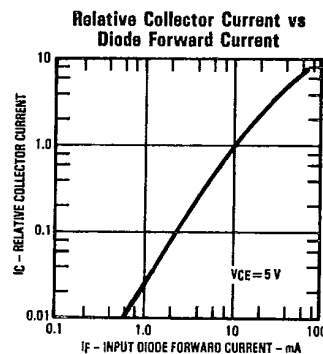
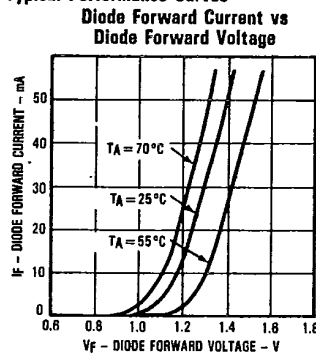
Forward DC Current	60 mA
Peak Forward Current (1 μs pulse, 300 pps)	3.0 A
Reverse Voltage	3.0 V
Power Dissipation (25°C)	100 mW ⁽³⁾

Output Transistor

Power Dissipation	150 mW ⁽⁴⁾
BIBRICEO	30 V
VIBRICEO	50 V
VIBRICEO	5.0 V

Notes: (1) Measured with input diode leads shorted together and output leads shorted together. (2) RMA flux is recommended. Duration can be extended to 10 sec. max. when flow soldering. (3) Derate linearly 1.33 mW/°C above 25°C. (4) Derate linearly 2.0 mW/°C above 25°C.

Typical Performance Curves



Types OPI2152, OPI2252

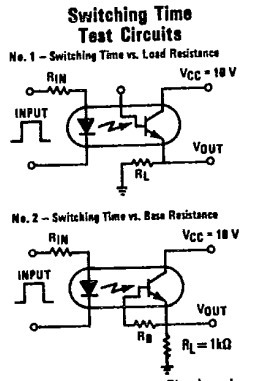
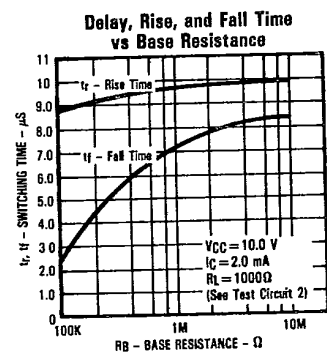
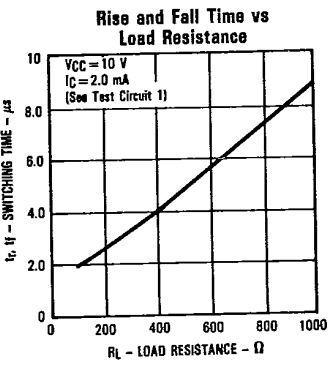
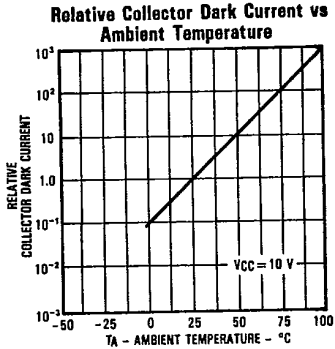
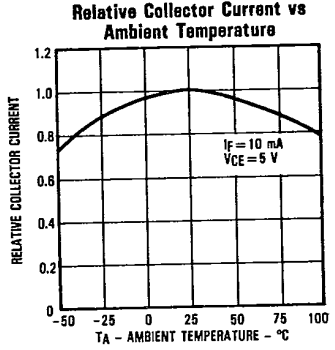
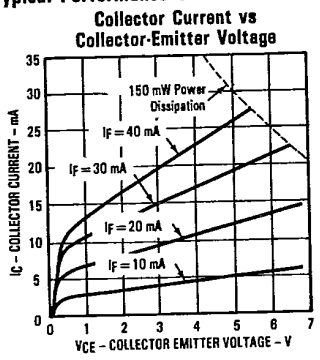
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Electrical Characteristics (TA = 25°C unless otherwise noted)

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
Input Diode						
V _F	Forward Voltage			1.50	V	I _F = 10.0 mA
V _{BR} (R)	Reverse Breakdown Voltage	3.0			V	I _R = 10.0 μA
I _R	Reverse Leakage Current			10.0	μA	V _R = 3.0 V
Output Phototransistor						
V _{BR} (CEO)	Collector-to-Emitter Breakdown Voltage	30			V	I _C = 1.00 mA
V _{BR} (ECO)	Emitter-to-Collector Breakdown Voltage	5.0			V	I _E = 10.0 μA
V _{BR} (CBO)	Collector-to-Base Breakdown Voltage	50			V	I _C = 10.0 μA
I _{CEO}	Collector-Emitter Dark Current		5.0	50	nA	V _{CE} = 10.0 V
I _{CBO}	Collector-Base Dark Current			20	nA	V _{CB} = 10.0 V
C _{CE}	Capacitance Collector-to-Emitter		8.0		pF	V _{CE} = 0
h _{FE}	DC Current Gain		250			V _{CE} = 5.0 V, I _C = 100 μA
Coupled						
I _C /I _F	DC Current Transfer Ratio	20	40		%	I _F = 10.0 mA, V _{CE} = 5.0 V
V _{CE} (SAT)	Collector-to-Emitter Saturation Voltage			0.40	V	I _F = 10.0 mA, I _C = 500 μA
V _{ISO}	Isolation Voltage OPI2152 OPI2252	1500 2500			VDC	See Note 1
R _{IO}	Input-to-Output Resistance	10 ¹¹			Ω	V _{IO} = 500 V, See Note 1
C _{IO}	Input-to-Output Capacitance		2.0		pF	f = 1.00 MHz, See Note 1
t _r	Output Rise Time		2.0		μs	V _{CC} = 10.0 V, I _C = 2.0 mA
t _f	Output Fall Time		2.0		μs	R _L = 100Ω, See Test Circuit



Typical Performance Curves



TRW reserves the right to make changes at any time in order to improve design and to supply the best product possible. Plastic color may vary.
 Optoelectronics Division, TRW Electronic Components Group, 1215 W. Crosby Rd., Carrollton, TX 75006 (214) 323-2200, TLX 6716032 or 215849
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